REMARKS

The Official Action mailed August 13, 2002 has been received and its contents carefully noted. A *Notice of Appeal* and *One Month Extension of Time* were filed December 13, 2002. The enclosed *Preliminary Amendment* and *Request for Continued Examination* is filed within 2 months of the filing of the *Notice of Appeal* and thus is believed to be timely filed.

Claims 1-20 were pending in the subject application. Claims 5 and 10-20 have been canceled and new claims 21-63 are added herewith to recite additional protection to which applicants are entitled. Therefore, claims 1-4, 6-9 and 21-63 are now pending in the subject application of which claims 1, 6, 21, 28, 35, 42, 49, 56, and 60 are independent. For the reasons set forth in detail below, all claims are believed to be in condition for allowance and favorable consideration is requested.

The Official Action mailed August 13, 2002 first rejects claims 5, 10, 15 and 20 under the doctrine of double patenting. In response, these claims have been canceled and thus this rejection is moot.

The Official Action next rejects claims 1, 2, 4, 6, 7 and 9 as anticipated by U.S. Patent 5,216,491 to Yamamoto. Specifically, the Official Action asserts that the "ground" potential reads on potential VB in Yamamoto. It is well established that "a claim is anticipated only if each and every element as set forth in the claim is found, either expressly or inherently described, in a single prior art reference." *Verdegaal Bros. v. Union Oil Co. of California*, 814 F.2d 628, 631, 2 USPQ2d 1051, 1053 (Fed. Cir. 1987).

Independent claims 1 and 6 have been amended herewith to recite that the optical sensor (3000) has first and second electrodes, the first electrode of the optical sensor is electrically connected to a first electrode of a capacitor (3002) and the second electrode of the optical sensor is electrically connected to a bias terminal (3007), which are supported in Figure 3 of the subject application. Although Yamamoto may teach potential VB in Figure 3, it appears that Yamamoto fails to disclose or suggest that a second electrode of the capacitor is at a ground potential as recited in claims 1 and 6.

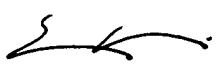
Therefore, since Yamamoto fails to disclose each and every element recited in the claims, it is respectfully submitted that Yamamoto cannot anticipate the claims and favorable reconsideration is requested.

The remaining rejections in the Official Action are believed to be overcome for the above reasons or are directed to canceled claims and are therefore moot. Favorable reconsideration and withdrawal of these rejections is requested.

Finally, new claims 21-63 are added to recite additional protection to which applicant is entitled. Claims 21-55 recite the formation of a bottom gate type TFT having a crystallized semiconductor layer, the formation of a second amorphous semiconductor layer on the crystallized semiconductor layer, and the formation of a transparent conductive film on the second amorphous layer. These claims are supported by at least Figures 1A to 2B and Embodiments 1, 2, 4 and 5 of the specification. It is respectfully submitted that these claims are patentable over the prior art of record and favorable consideration is requested. New claims 56-63 recite similar subject matter to claims 1 and 6 and are thus believed to be allowable for the same reasons as noted above. Favorable consideration is again requested for these claims.

Should the Examiner believe that anything further would be desirable to place this application in better condition for allowance, the Examiner is invited to contact Applicant's undersigned attorney at the telephone number listed below.

Respectfully submitted,



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VERSION WITH MARKINGS TO SHOW CHANGES MADE

1. (Amended) An image sensor comprising:

an optical sensor having a first electrode and a second electrode formed over a substrate;

a thin film transistor electrically connected to a first electrode of said optical sensor in series; and

a capacitor having a first electrode and a second electrode, wherein said first electrode of said capacitor is electrically connected to said first electrode of said optical sensor between said optical sensor and said thin film transistor, [and] wherein said second electrode of said capacitor is at a ground potential, and wherein said second electrode of said optical sensor is electrically connected to a bias terminal.

6. (Amended) An image sensor comprising:

an optical sensor having a first electrode and a second electrode formed over a substrate;

a thin film transistor electrically connected to a first electrode of said optical sensor in series;

a capacitor having a first electrode and a second electrode, wherein said first electrode of said capacitor is electrically connected to said first electrode of said optical sensor between said optical sensor and said thin film transistor, [and] wherein said second electrode of said capacitor is at a ground potential, and wherein said second electrode of said optical sensor is electrically connected to a bias terminal; and

an amplifier electrically connected to said thin film transistor in series.